BUH615D

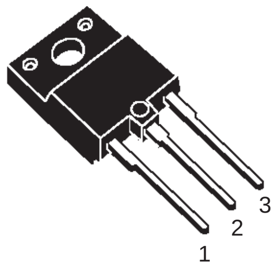
HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

- STMicroelectronics PREFERRED SALESTYPE
- HIGH VOLTAGE CAPABILITY
- NPN TRANSISTOR WITH INTEGRATED FREEWHEELING DIODE
- U.L. RECOGNISED ISOWATT218 PACKAGE (U.L. FILE # E81734 (N))

APPLICATIONS:
- HORIZONTAL DEFLECTION FOR COLOUR TV

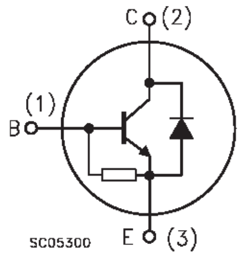
DESCRIPTION
The BUH615D is manufactured using Multiepitaxial Mesa technology for cost-effective high performance and uses a Hollow Emitter structure to enhance switching speeds.

The BUH series is designed for use in horizontal deflection circuits in televisions and monitors.



ISOWATT218

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage (I_E = 0)	1500	V
V_{CEO}	Collector-Emitter Voltage (I_B = 0)	700	V
V_{EBO}	Emitter-Base Voltage (I_C = 0)	5	V
I_C	Collector Current	8	A
I_{CM}	Collector Peak Current (t_p < 5 ms)	12	A
I_B	Base Current	5	A
I_{BM}	Base Peak Current (t_p < 5 ms)	8	A
P_{tot}	Total Dissipation at T_c = 25 ^oC	55	W
T_{stg}	Storage Temperature	-65 to 150	^oC
T_j	Max. Operating Junction Temperature	150	^oC

THERMAL DATA

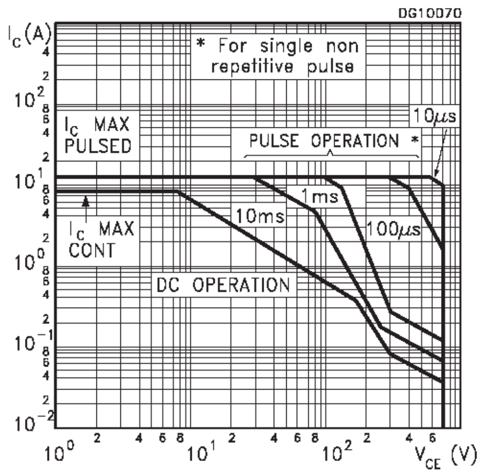
$R_{thj-case}$	Thermal Resistance Junction-case Max	2.3	$^oC/W$

ELECTRICAL CHARACTERISTICS (T_{case} = 25 ^oC unless otherwise specified)

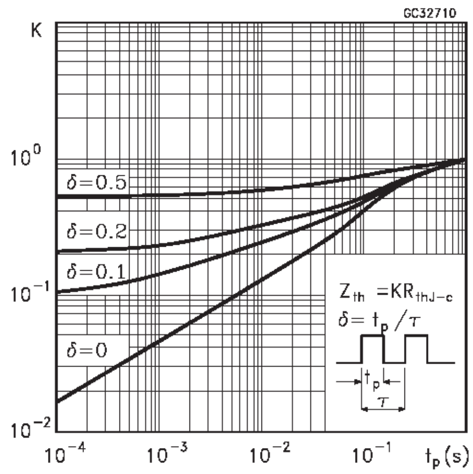
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CES}	Collector Cut-off Current (V_{BE} = 0)	V_{CE} = 1500 V V_{CE} = 1500 V T_j = 125 ^oC			0.2 2	mA mA
I_{EBO}	Emitter Cut-off Current (I_C = 0)	V_{EB} = 5 V			300	mA
$V_{CE(sat)}$*	Collector-Emitter Saturation Voltage	I_C = 6 A I_B = 2.5 A			1.5	V
$V_{BE(sat)}$*	Base-Emitter Saturation Voltage	I_C = 6 A I_B = 2.5 A			1.3	V
h_{FE}*	DC Current Gain	I_C = 6 A V_{CE} = 5 V	4		9	
t_s t_f	RESISTIVE LOAD Storage Time Fall Time	V_{CC} = 400 V I_C = 6 A I_{B1} = 1.5 A I_{B2} = -3 A		2.7 190	3.9 280	µs ns
t_s t_f	INDUCTIVE LOAD Storage Time Fall Time	I_C = 6 A f = 15625 Hz I_{B1} = 1.25 A I_{B2} = -3 A $V_{ceflyback} = 1050 \sin\left(\frac{\pi}{10} 10^6\right) t$ V		2.3 350		µs ns
t_s t_f	INDUCTIVE LOAD Storage Time Fall Time	I_C = 6 A f = 31250 Hz I_{B1} = 1.5 A I_{B2} = -3 A $V_{ceflyback} = 1200 \sin\left(\frac{\pi}{5} 10^6\right) t$ V		2.3 200		µs ns
V_f	Diode Forward Voltage	IF = 5 A			2	V

∗ Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %

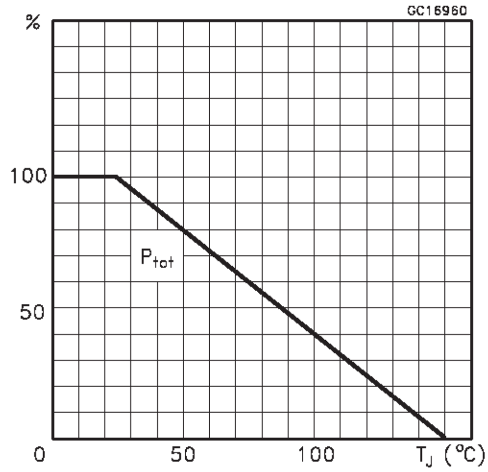
Safe Operating Area



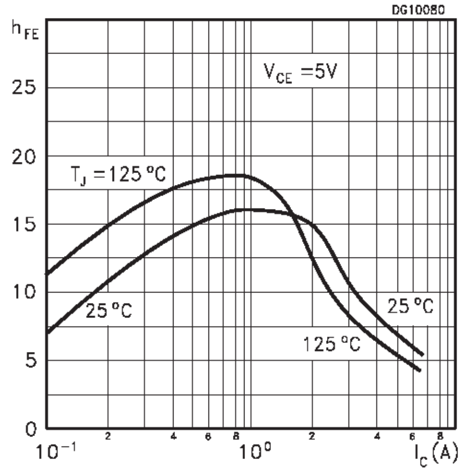
Thermal Impedance



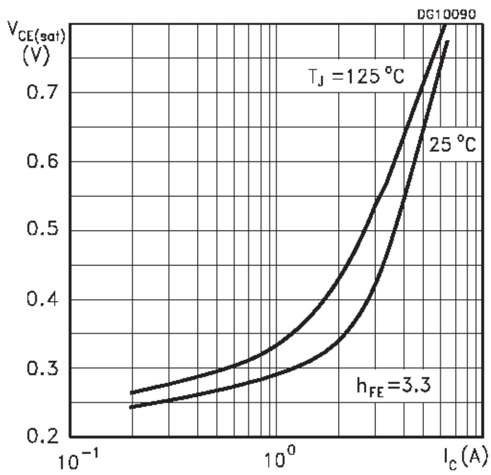
Derating Curve



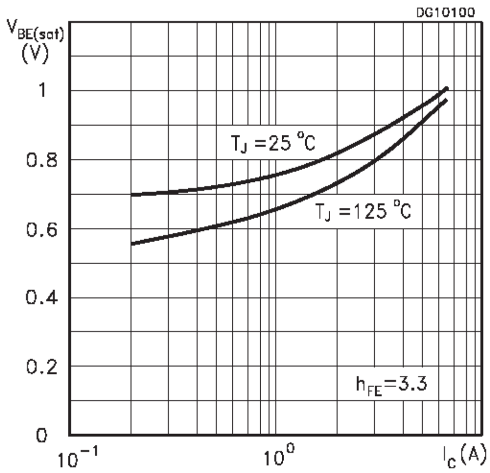
DC Current Gain



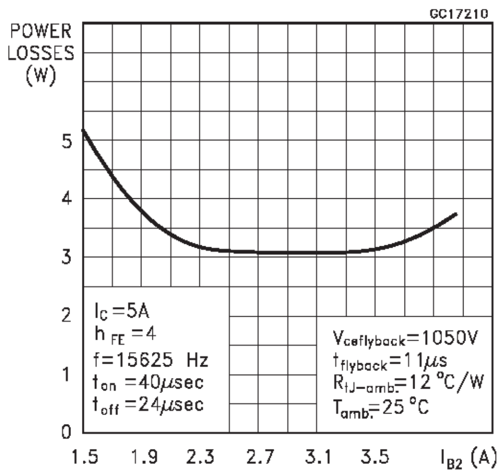
Collector Emitter Saturation Voltage



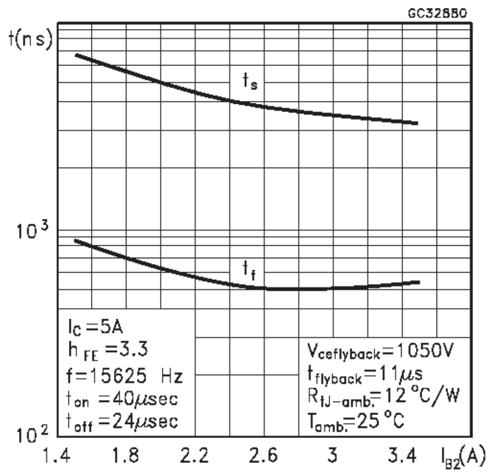
Base Emitter Saturation Voltage



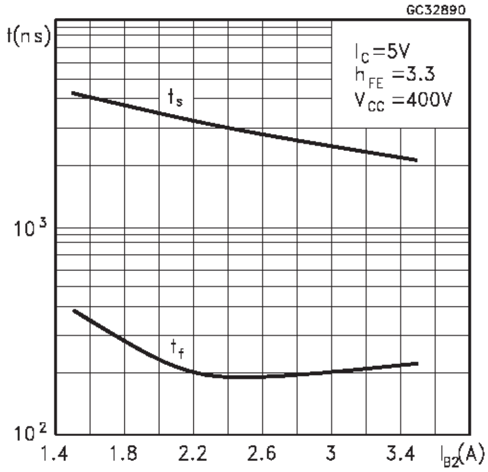
Power Losses at 16KHz



Switching Time Inductive Load at 16KHz



Switching Time Resistive Load



BASE DRIVE INFORMATION

A fundamental parameter of high voltage power transistors like those used in the horizontal deflection stage is their junction temperature T_j, which, in turn, depends on the power dissipation. This parameter turns out to influence the system reliability under normal operation. Based on that, STMicroelectronics has introduced a new dynamic, application-oriented characterization differing from the traditional data given in most datasheets.

In order to saturate the power switch and reduce conduction losses, adequate direct base current I_{B1} has to be provided for the lowest gain h_{FE} at T_j = 100 ^oC (line scan phase). On the other hand, negative base current I_{B2} must be provided for the transistor to be turned off (retrace phase). Most of the dissipation, especially in the deflection application, occurs at switch-off so it is essential to determine the value of I_{B2} which minimizes power losses, fall time t_f and, consequently, T_j. A new set of curves have been defined to give total power losses, t_s and t_f as a function of I_{B2} at both 16 KHz and 32 KHz scanning frequencies for choosing the optimum negative drive. The test circuit is illustrated in fig. 1.

Inductance L_1 serves to control the slope of the negative base current I_{B2} in order that excess carriers in the collector recombine when base current is still present, thus avoiding any tailing phenomenon in the collector current. This effect is, in any case, markedly reduced intrinsically by adopting the hollow emitter technology.

The values of L and C are calculated from the following equations:

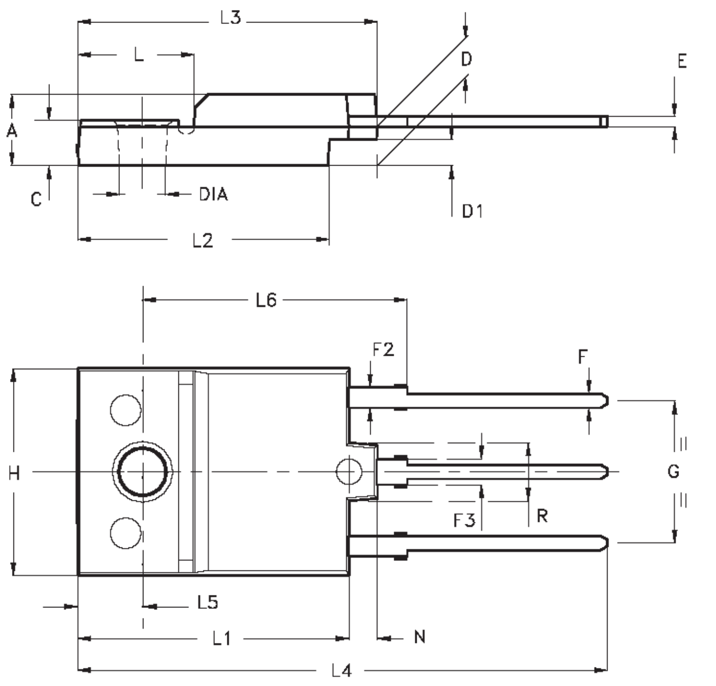
$$\frac{1}{2} L \, (I_C)^2 = \frac{1}{2} C \, (V_{CEfly})^2$$

$$\omega = 2 \, \pi f = \frac{1}{\sqrt{L \, C}}$$

Where I_C= operating collector current, V_{CEfly}= flyback voltage, f= frequency of oscillation during retrace.

ISOWATT218 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	5.35		5.65	0.211		0.222
C	3.30		3.80	0.130		0.150
D	2.90		3.10	0.114		0.122
D1	1.88		2.08	0.074		0.082
E	0.75		0.95	0.030		0.037
F	1.05		1.25	0.041		0.049
F2	1.50		1.70	0.059		0.067
F3	1.90		2.10	0.075		0.083
G	10.80		11.20	0.425		0.441
H	15.80		16.20	0.622		0.638
L		9			0.354	
L1	20.80		21.20	0.819		0.835
L2	19.10		19.90	0.752		0.783
L3	22.80		23.60	0.898		0.929
L4	40.50		42.50	1.594		1.673
L5	4.85		5.25	0.191		0.207
L6	20.25		20.75	0.797		0.817
N	2.1		2.3	0.083		0.091
R		4.6			0.181	
DIA	3.5		3.7	0.138		0.146



- Weight : 4.9 g (typ.)
- Maximum Torque (applied to mounting flange) Recommended 0.8 Nm; Maximum: 1 Nm
- The side of the dissipator must be flat within 80 µm

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